

Atsushi Ogura

List of Publications by Year in descending order

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308
papers

3,240
citations

218677

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254184

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docs citations

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times ranked

2591
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#	ARTICLE	IF	CITATIONS
1	Neoadjuvant (Chemo)radiotherapy With Total Mesorectal Excision Only Is Not Sufficient to Prevent Lateral Local Recurrence in Enlarged Nodes: Results of the Multicenter Lateral Node Study of Patients With Low cT3/4 Rectal Cancer. <i>Journal of Clinical Oncology</i> , 2019, 37, 33-43.	1.6	308
2	Lateral Nodal Features on Restaging Magnetic Resonance Imaging Associated With Lateral Local Recurrence in Low Rectal Cancer After Neoadjuvant Chemoradiotherapy or Radiotherapy. <i>JAMA Surgery</i> , 2019, 154, e192172.	4.3	141
3	UV-Raman Spectroscopy System for Local and Global Strain Measurements in Si. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 3007-3011.	1.5	85
4	Gas source silicon molecular beam epitaxy using silane. <i>Applied Physics Letters</i> , 1987, 51, 2213-2215.	3.3	80
5	Improvement in ferroelectricity of $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$ thin films using ZrO_2 seed layer. <i>Applied Physics Express</i> , 2017, 10, 081501.	2.4	63
6	HfO ₂ growth by low-pressure chemical vapor deposition using the $\text{Hf}(\text{N}(\text{C}_2\text{H}_5)_2)_4/\text{O}_2$ gas system. <i>Journal of Crystal Growth</i> , 2001, 233, 292-297.	1.5	62
7	Feasibility of Laparoscopic Total Mesorectal Excision with Extended Lateral Pelvic Lymph Node Dissection for Advanced Lower Rectal Cancer after Preoperative Chemoradiotherapy. <i>World Journal of Surgery</i> , 2017, 41, 868-875.	1.6	62
8	Pattern of programmed cell death-ligand 1 expression and CD8-positive T-cell infiltration before and after chemoradiotherapy in rectal cancer. <i>European Journal of Cancer</i> , 2018, 91, 11-20.	2.8	55
9	Ferroelectricity of $\text{Hf}_x\text{Zr}_{1-x}\text{O}_2$ thin films fabricated by 300°C low temperature process with plasma-enhanced atomic layer deposition. <i>Microelectronic Engineering</i> , 2019, 215, 111013.	2.4	55
10	Multi-layered MoS ₂ film formed by high-temperature sputtering for enhancement-mode nMOSFETs. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 04DN08.	1.5	53
11	Using tetrakis-diethylamido-hafnium for HfO ₂ thin-film growth in low-pressure chemical vapor deposition. <i>Thin Solid Films</i> , 2002, 406, 215-218.	1.8	46
12	Skeletal muscle loss is an independent negative prognostic factor in patients with advanced lower rectal cancer treated with neoadjuvant chemoradiotherapy. <i>PLoS ONE</i> , 2018, 13, e0195406.	2.5	46
13	Improvement in ferroelectricity of $\text{Hf}_x\text{Zr}_{1-x}\text{O}_2$ thin films using top- and bottom-ZrO ₂ nucleation layers. <i>APL Materials</i> , 2019, 7, .	5.1	46
14	Analysis of Intra-Grain Defects in Multicrystalline Silicon Wafers by Photoluminescence Mapping and Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L641-L643.	1.5	43
15	Miniaturized planar Si-nanowire micro-thermoelectric generator using exuded thermal field for power generation. <i>Science and Technology of Advanced Materials</i> , 2018, 19, 443-453.	6.1	43
16	Low-Carrier-Density Sputtered MoS ₂ Film by Vapor-Phase Sulfurization. <i>Journal of Electronic Materials</i> , 2018, 47, 3497-3501.	2.2	36
17	Transverse-optical phonons excited in Si using a high-numerical-aperture lens. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	34
18	Role of i-aSi:H Layers in aSi:H/cSi Heterojunction Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2013, 3, 1149-1155.	2.5	33

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19	The significance of extended lymphadenectomy for colorectal cancer with isolated synchronous extraregional lymph node metastasis. <i>Asian Journal of Surgery</i> , 2017, 40, 254-261.	0.4	31
20	Photoluminescence Analysis of Iron Contamination Effect in Multicrystalline Silicon Wafers for Solar Cells. <i>Journal of Electronic Materials</i> , 2010, 39, 747-750.	2.2	29
21	Channel strain analysis in high-performance damascene-gate p-metal-oxide-semiconductor field effect transistors using high-spatial resolution Raman spectroscopy. <i>Journal of Applied Physics</i> , 2010, 107, .	2.5	29
22	Interface engineering for the passivation of c-Si with O ₃ -based atomic layer deposited AlO _x for solar cell application. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	29
23	Investigation on antireflection coating for high resistance to potential-induced degradation. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 03CE01.	1.5	29
24	Nanoscale Wet Etching of Physical-Vapor-Deposited Titanium Nitride and Its Application to Sub-30-nm-Gate-Length Fin-Type Double-Gate Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Fabrication. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 06GH18.	1.5	27
25	Safety of Laparoscopic Pelvic Exenteration with Urinary Diversion for Colorectal Malignancies. <i>World Journal of Surgery</i> , 2016, 40, 1236-1243.	1.6	27
26	Improving crystalline quality of sputtering-deposited MoS ₂ thin film by postdeposition sulfurization annealing using (t-C ₄ H ₉) ₂ S ₂ . <i>Japanese Journal of Applied Physics</i> , 2016, 55, 04EJ07.	1.5	26
27	Quantitative relationship between sputter-deposited-MoS ₂ properties and underlying-SiO ₂ surface roughness. <i>Applied Physics Express</i> , 2017, 10, 041202.	2.4	26
28	Novel technique for Si epitaxial lateral overgrowth: Tunnel epitaxy. <i>Applied Physics Letters</i> , 1989, 55, 2205-2207.	3.3	25
29	Positive and negative dipole layer formation at high-k/SiO ₂ interfaces simulated by classical molecular dynamics. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 04EB03.	1.5	25
30	Characterization of Strain for High-Performance Metalâ€“Oxideâ€“Semiconductor Field-Effect-Transistor. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 2538-2543.	1.5	24
31	Evaluation of defects generation in crystalline silicon ingot grown by cast technique with seed crystal for solar cells. <i>Journal of Applied Physics</i> , 2012, 111, 074505.	2.5	24
32	Improvement of SiO ₂ /Si Interface Flatness by Postâ€“Oxidation Anneal. <i>Journal of the Electrochemical Society</i> , 1991, 138, 807-810.	2.9	23
33	A Comparative Study of Nitrogen Gas Flow Ratio Dependence on the Electrical Characteristics of Sputtered Titanium Nitride Gate Bulk Planar Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors and Fin-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 05DC01.	1.5	23
34	Interaction between Metal Impurities and Small-Angle Grain Boundaries on Recombination Properties in Multicrystalline Silicon for Solar Cells. <i>Applied Physics Express</i> , 2012, 5, 042301.	2.4	23
35	Local recurrences in western low rectal cancer patients treated with or without lateral lymph node dissection after neoadjuvant (chemo)radiotherapy: An international multi-centre comparative study. <i>European Journal of Surgical Oncology</i> , 2021, 47, 2441-2449.	1.0	21
36	Infrared studies of silicon oxide formation in silicon wafers implanted with oxygen. <i>Applied Physics Letters</i> , 1998, 72, 2853-2855.	3.3	20

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37	Annealing properties of defects during Si-on-insulator fabrication by low-dose oxygen implantation studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2000, 87, 1659-1665.	2.5	20
38	Vapor Pressure of Hf and Si Precursors for Hf _x Si _{1-x} O ₂ Deposition Evaluated by a Saturated Gas Technique. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 966-967.	1.5	20
39	Nitrogen Gas Flow Ratio and Rapid Thermal Annealing Temperature Dependences of Sputtered Titanium Nitride Gate Work Function and Their Effect on Device Characteristics. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 2433.	1.5	20
40	Evaluation of depth profile of defects in ultrathin Si film on buried SiO ₂ formed by implanted oxygen. <i>Applied Physics Letters</i> , 1996, 69, 1367-1369.	3.3	19
41	Hf _{1-x} Si _x O ₂ deposition by metal organic chemical vapor deposition using the Hf(NEt ₂) ₄ /SiH(NEt ₂) ₃ /O ₂ gas system. <i>Thin Solid Films</i> , 2002, 416, 208-211.	1.8	19
42	Formation of a buried oxide film at the damage peak induced by oxygen implantation into a Si substrate. <i>Applied Physics Letters</i> , 1999, 74, 2188-2190.	3.3	18
43	Effects of deposition conditions on step-coverage quality in low-pressure chemical vapor deposition of HfO ₂ . <i>Journal of Crystal Growth</i> , 2002, 235, 365-370.	1.5	18
44	Biaxial stress evaluation in GeSn film epitaxially grown on Ge substrate by oil-immersion Raman spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 091301.	1.5	18
45	Measurement of in-plane and depth strain profiles in strained-Si substrates. <i>Solid-State Electronics</i> , 2007, 51, 219-225.	1.4	17
46	High-mobility and low-parasitic resistance characteristics in strained Ge nanowire pMOSFETs with metal source/drain structure formed by doping-free processes. , 2012, , .		17
47	Advantage in solar cell efficiency of high-quality seed cast mono Si ingot. <i>Applied Physics Express</i> , 2015, 8, 062301.	2.4	17
48	Characteristics of Oxide TFT Using Carbon-Doped In ₂ O ₃ Thin Film Fabricated by Low-Temperature ALD Using Ethylcyclopentadienyl Indium (In TM -EtCp) and H ₂ O & O ₃ . <i>ECS Transactions</i> , 2019, 92, 3-13.	0.5	17
49	Extension of Dose Window for Low-Dose Separation by Implanted Oxygen. <i>Journal of the Electrochemical Society</i> , 1998, 145, 1735-1737.	2.9	16
50	Ni Precursor for Chemical Vapor Deposition of NiSi. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 1833-1836.	1.5	16
51	Quantitative analysis of impurities in solar-grade Si by photoluminescence spectroscopy around 20 K. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 792-795.	0.8	16
52	Plasma-enhanced chemical-vapor deposition of silicon nitride film for high resistance to potential-induced degradation. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 08KD12.	1.5	16
53	Properties of single-layer MoS ₂ film fabricated by combination of sputtering deposition and post deposition sulfurization annealing using (t-C ₄ H ₉) ₂ S ₂ . <i>Japanese Journal of Applied Physics</i> , 2016, 55, 06GF01.	1.5	16
54	Improved leakage current properties of ZrO ₂ /(Ta/Nb) _x Al ₂ O ₃ /ZrO ₂ nanolaminate insulating stacks for dynamic random access memory capacitors. <i>Thin Solid Films</i> , 2018, 655, 48-53.	1.8	16

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55	Study of Strain Induction for Metal-Oxide-Semiconductor Field-Effect Transistors using Transparent Dummy Gates and Stress Liners. Japanese Journal of Applied Physics, 2009, 48, 066508.	1.5	15
56	Study of the Degradation of p-n Diode Characteristics Caused by Small-Angle Grain Boundaries in Multi-Crystalline Silicon Substrate for Solar Cells. Japanese Journal of Applied Physics, 2009, 48, 121202.	1.5	15
57	Channel-Stress Enhancement Characteristics for Scaled pMOSFETs by Using Damascene Gate With Top-Cut Compressive Stress Liner and eSiGe. IEEE Transactions on Electron Devices, 2009, 56, 2778-2784.	3.0	15
58	In- and out-diffusion of oxygen during the buried-oxide formation in oxygen-implanted silicon. Journal of Applied Physics, 2000, 87, 7782-7787.	2.5	14
59	Microscopic Distributions of Light Elements and Their Precipitates in Multicrystalline Silicon for Solar Cells. Japanese Journal of Applied Physics, 2010, 49, 110202.	1.5	14
60	Fin-Height Effect on Poly-Si/PVD-TiN Stacked-Gate FinFET Performance. IEEE Transactions on Electron Devices, 2012, 59, 647-653.	3.0	14
61	Butterfly-shaped distribution of SiN precipitates in multi-crystalline Si for solar cells. Journal of Crystal Growth, 2013, 377, 37-42.	1.5	14
62	Minority Carrier Recombination Properties of Crystalline Defect on Silicon Surface Induced by Plasma Enhanced Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2016, 5, Q253-Q256.	1.8	14
63	Effects of Aluminum in Metallization Paste on the Electrical Losses in Bifacial N-type Crystalline Silicon Solar Cells. Energy Procedia, 2016, 98, 106-114.	1.8	14
64	Patient-centered outcomes to decide treatment strategy for patients with low rectal cancer. Journal of Surgical Oncology, 2016, 114, 630-636.	1.7	14
65	Low-temperature grain growth of initially ~100% textured polycrystalline silicon films amorphized by silicon ion implantation with normal incident angle. Journal of Applied Physics, 1986, 59, 289-291.	2.5	13
66	Crystallinity estimation of thin silicon-on-insulator layers by means of diffractometry using a highly parallel X-ray microbeam. Journal of Synchrotron Radiation, 2006, 13, 373-377.	2.4	13
67	Evaluation of Anisotropic Strain Relaxation in Strained Silicon-on-Insulator Nanostructure by Oil-Immersion Raman Spectroscopy. Japanese Journal of Applied Physics, 2012, 51, 02BA03.	1.5	13
68	GeSn Film Deposition Using Metal Organic Chemical Vapor Deposition. ECS Transactions, 2013, 53, 245-250.	0.5	13
69	Low-pressure chemical vapor deposition of TaCN films by pyrolysis of ethylamido-tantalum. Journal of Crystal Growth, 2000, 220, 604-609.	1.5	12
70	Formation of patterned buried insulating layer in Si substrates by He+ implantation and annealing in oxidation atmosphere. Applied Physics Letters, 2003, 82, 4480-4482.	3.3	12
71	Mobility and Velocity Enhancement Effects of High Uniaxial Stress on Si (100) and (110) Substrates for Short-Channel pFETs. IEEE Transactions on Electron Devices, 2010, 57, 1295-1300.	3.0	12
72	Experimental Study of Physical-Vapor-Deposited Titanium Nitride Gate with An n ⁺ -Polycrystalline Silicon Capping Layer and Its Application to 20 nm Fin-Type Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC14.	1.5	12

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73	Investigation of Phonon Deformation Potentials in Si _{1-x} Ge _x by Oil-Immersion Raman Spectroscopy. Applied Physics Express, 2012, 5, 111301.	2.4	12
74	Variability Analysis of Scaled Crystal Channel and Poly-Si Channel FinFETs. IEEE Transactions on Electron Devices, 2012, 59, 573-581.	3.0	12
75	Endoscopic evaluation of clinical response after preoperative chemoradiotherapy for lower rectal cancer: the significance of endoscopic complete response. International Journal of Colorectal Disease, 2015, 30, 367-373.	2.2	12
76	Large Scale Uniformity of Sputtering Deposited Single- and Few-Layer MoS ₂ Investigated by XPS Multipoint Measurements and Histogram Analysis of Optical Contrast. ECS Journal of Solid State Science and Technology, 2016, 5, Q3012-Q3015.	1.8	12
77	Effects of thermal budget in n-type bifacial solar cell fabrication processes on effective lifetime of crystalline silicon. AIP Advances, 2017, 7, .	1.3	12
78	Quantification of C in Si by photoluminescence at liquid N temperature after electron irradiation. Applied Physics Express, 2017, 10, 046602.	2.4	12
79	Determination of phonon deformation potentials and strain-shift coefficients in Ge-rich Si _{1-x} Ge _x using bulk Ge-rich Si _{1-x} Ge _x crystals and oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 106601.	1.5	12
80	Endoscopic criteria to evaluate tumor response of rectal cancer to neoadjuvant chemoradiotherapy using magnifying chromoendoscopy. European Journal of Surgical Oncology, 2018, 44, 1247-1253.	1.0	12
81	Ge ₂ Sb ₂ Te ₅ Film Fabrication by Tellurization of Chemical Vapor Deposited GeSb. Japanese Journal of Applied Physics, 2013, 52, 128006.	1.5	11
82	Chemical Synthesis of Multilayered Nanostructured Perovskite Thin Films with Dielectric Features for Electric Capacitors. ACS Applied Nano Materials, 2018, 1, 915-921.	5.0	11
83	Oxygen-related defects and their annealing behavior in low-dose Separation-by-Implanted OXYgen (SIMOX) wafers studied by slow positron beams. Applied Surface Science, 2002, 194, 112-115.	6.1	10
84	Evaluation of local strain in Si using UV-Raman spectroscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 206-211.	3.5	10
85	Evaluation of Strained-Silicon by Electron Backscattering Pattern Measurement: Comparison Study with UV-Raman Measurement and Edge Force Model Calculation. Japanese Journal of Applied Physics, 2011, 50, 010111.	1.5	10
86	Demonstration of Split-Gate Type Trigate Flash Memory With Highly Suppressed Over-Erase. IEEE Electron Device Letters, 2012, 33, 345-347.	3.9	10
87	Investigation of dislocations in Nb-doped SrTiO ₃ by electron-beam-induced current and transmission electron microscopy. Applied Physics Letters, 2015, 106, 102109.	3.3	10
88	Sputter-Deposited-MoS ₂ MISFETs With Top-Gate and Al ₂ O ₃ Passivation Under Low Thermal Budget for Large Area Integration. IEEE Journal of the Electron Devices Society, 2018, 6, 1246-1252.	2.1	10
89	Control of dipole properties in high-k and SiO ₂ stacks on Si substrates with tricolor superstructure. Applied Physics Letters, 2018, 113, .	3.3	10
90	Effect of additives in electrode paste of p-type crystalline Si solar cells on potential-induced degradation. Solar Energy, 2019, 188, 1292-1297.	6.1	10

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91	Germanium film on SiO ₂ with a ~100% texture deposited by the rf sputtering technique. Applied Physics Letters, 1985, 47, 1059-1061.	3.3	9
92	Defects in silicon-on-insulator wafers and their hydrogen interaction studied by monoenergetic positron beams. Journal of Applied Physics, 2002, 91, 6488.	2.5	9
93	Ni Thin Film Deposition from Tetrakis(trifluorophosphine)-Nickel. Japanese Journal of Applied Physics, 2005, 44, L315-L317.	1.5	9
94	Evaluation of Strain in Si-on-Insulator Substrate Induced by Si ₃ N ₄ Capping Film. Japanese Journal of Applied Physics, 2008, 47, 1465-1468.	1.5	9
95	Improvement of CVD SiO ₂ by Post Deposition Microwave Plasma Treatment. ECS Transactions, 2009, 19, 45-51.	0.5	9
96	Quantitative Analysis of Stress Relaxation in Transmission Electron Microscopy Samples by Raman Spectroscopy with a High-Numerical Aperture Lens. Japanese Journal of Applied Physics, 2011, 50, 04DA06.	1.5	9
97	Stress evaluation in thin strained-Si film by polarized Raman spectroscopy using localized surface plasmon resonance. Applied Physics Letters, 2012, 101, .	3.3	9
98	Donor-acceptor pair luminescence in B and P compensated Si co-doped with Ga. Journal of Applied Physics, 2013, 113, .	2.5	9
99	Growth of Ge Homoepitaxial Films by Metal-Organic Chemical Vapor Deposition Using t-C ₄ H ₉ GeH ₃ . ECS Journal of Solid State Science and Technology, 2015, 4, P152-P154.	1.8	9
100	Determination of low carbon concentration in Czochralski-grown Si crystals for solar cells by luminescence activation using electron irradiation. Japanese Journal of Applied Physics, 2017, 56, 070305.	1.5	9
101	Origin of room-temperature photoluminescence around C-line in electron-irradiated Si and its applicability for quantification of carbon. Applied Physics Express, 2018, 11, 041301.	2.4	9
102	Ferroelectricity of Hf _x Zr _{1-x} O ₂ Thin Films Fabricated Using TiN Stressor and ZrO ₂ Nucleation Techniques. ECS Transactions, 2018, 86, 31-38.	0.5	9
103	Malignant Features in Pretreatment Metastatic Lateral Lymph Nodes in Locally Advanced Low Rectal Cancer Predict Distant Metastases. Annals of Surgical Oncology, 2022, 29, 1194-1203.	1.5	9
104	Characterization of surface imperfections of silicon-on-insulator wafers by means of extremely asymmetric x-ray reflection topography. Applied Physics Letters, 1996, 68, 693-695.	3.3	8
105	Depth profiles of As and B implanted into Si-on-insulator substrates. Thin Solid Films, 2001, 397, 56-62.	1.8	8
106	Evaluation of HfO ₂ film structures deposited by metal-organic chemical vapor deposition using Hf(N(C ₂ H ₅) ₂) ₄ /O ₂ gas system. Thin Solid Films, 2003, 441, 161-164.	1.8	8
107	Characterization of strained Si wafers by X-ray diffraction techniques. Journal of Materials Science: Materials in Electronics, 2008, 19, 189-193.	2.2	8
108	Chemical Vapor Deposition of GeSbTe Thin Films for Next-Generation Phase Change Memory. Japanese Journal of Applied Physics, 2010, 49, 05FF06.	1.5	8

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109	Evaluation of Anisotropic Biaxial Stress by Raman Spectroscopy with a High Numerical Aperture Immersion Objective Lens. Japanese Journal of Applied Physics, 2010, 49, 04DA21.	1.5	8
110	Complementary Distribution of NN and NNO Complexes in Cast-Grown Multicrystalline Silicon for Photovoltaic Cells. Applied Physics Express, 2011, 4, 115601.	2.4	8
111	Electrical field analysis of metal-surface plasmon resonance using a biaxially strained Si substrate. Journal of Raman Spectroscopy, 2014, 45, 414-417.	2.5	8
112	Ge incorporated epitaxy of (110) rutile TiO ₂ on (100) Ge single crystal at low temperature by pulsed laser deposition. Thin Solid Films, 2015, 591, 105-110.	1.8	8
113	Examination of phonon deformation potentials for accurate strain measurements in silicon-germanium alloys with the whole composition range by Raman spectroscopy. Japanese Journal of Applied Physics, 2016, 55, 026602.	1.5	8
114	Improvement of smooth surface of RuO ₂ bottom electrode on Al ₂ O ₃ buffer layer and characteristics of RuO ₂ /TiO ₂ /Al ₂ O ₃ /TiO ₂ /RuO ₂ capacitors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	8
115	Evaluation of Laterally Graded Silicon Germanium Wires for Thermoelectric Devices Fabricated by Rapid Melting Growth. ECS Transactions, 2018, 86, 87-93.	0.5	8
116	Effects of substrate self-bias and nitrogen flow rate on non-polar AlN film growth by reactive sputtering. Japanese Journal of Applied Physics, 2019, 58, SDDG07.	1.5	8
117	Effects of damages induced by indium-tin-oxide reactive plasma deposition on minority carrier lifetime in silicon crystal. AIP Advances, 2019, 9, .	1.3	8
118	Atomic mass dependency of a localized phonon mode in SiGe alloys. AIP Advances, 2021, 11, .	1.3	8
119	Characterizing Metal-Oxide Semiconductor Structures Consisting of HfSiO _x Gate Dielectrics using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2004, 43, 1254-1259.	1.5	7
120	Investigation of Thermal Stability of TiN Film Formed by Atomic Layer Deposition Using Tetrakis(dimethylamino)titanium Precursor for Metal-Gate Metal-Oxide Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2010, 49, 04DA16.	1.5	7
121	Impact of Light-Element Impurities on Crystalline Defect Generation in Silicon Wafer. Japanese Journal of Applied Physics, 2012, 51, 02BP08.	1.5	7
122	Molecular dynamics study on the formation of dipole layer at high-k/SiO ₂ interfaces. Japanese Journal of Applied Physics, 2014, 53, 08LB02.	1.5	7
123	Polarized photoluminescence imaging analysis around small-angle grain boundaries in multicrystalline silicon wafers for solar cells. Japanese Journal of Applied Physics, 2014, 53, 080303.	1.5	7
124	Origin of additional broad peaks in Raman spectra from thin germanium-rich silicon-germanium films. Applied Physics Express, 2016, 9, 071301.	2.4	7
125	Local anisotropic strain evaluation in thin Ge epitaxial film using SiGe stressor template grown on Ge substrate by selective ion implantation. Japanese Journal of Applied Physics, 2017, 56, 110313.	1.5	7
126	Characterization of Glass Frit in Conductive Paste for N-Type Crystalline Silicon Solar Cells. IEEE Journal of Photovoltaics, 2017, 7, 1313-1318.	2.5	7

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127	Superior subthreshold characteristics of gate-all-around p-type junctionless poly-Si nanowire transistor with ideal subthreshold slope. Japanese Journal of Applied Physics, 2020, 59, 070908.	1.5	7
128	Evaluation of plasma induced defects on silicon substrate by solar cell fabrication process. Japanese Journal of Applied Physics, 2020, 59, 071003.	1.5	7
129	Observation on laser-annealed silicon-insulator structures by cross-sectional transmission electron microscopy. Journal of Applied Physics, 1987, 62, 4170-4173.	2.5	6
130	High-speed video observation of laser recrystallization for semiconductor-insulator fabrication. Journal of Applied Physics, 1989, 65, 752-754.	2.5	6
131	Extremely thin and defect-free Si-insulator fabrication by tunnel epitaxy. Applied Physics Letters, 1990, 57, 2806-2807.	3.3	6
132	50-nm-Thick Silicon-Insulator Fabrication by Advanced Epitaxial Lateral Overgrowth: Tunnel Epitaxy. Journal of the Electrochemical Society, 1993, 140, 1125-1130.	2.9	6
133	Two-Dimensional Anisotropic Lattice Deformation Observed in a Commercially Available Strained-Si Wafer. Japanese Journal of Applied Physics, 2006, 45, 8542-8548.	1.5	6
134	Composition Control of Ni Silicide by Chemical Vapor Deposition Using Ni(PF ₃) ₄ and Si ₃ H ₈ . Japanese Journal of Applied Physics, 2007, 46, 474-477.	1.5	6
135	Evaluation of Ge_xSb_yTe_z Film Grown by Chemical Vapor Deposition. Materials Science Forum, 0, 725, 289-292.	0.3	6
136	Fabrication and Characterization of NOR-Type Tri-Gate Flash Memory with Improved Inter-Poly Dielectric Layer by Rapid Thermal Oxidation. Japanese Journal of Applied Physics, 2012, 51, 06FE19.	1.5	6
137	Formation of Si₂N₂O Microcrystalline Precipitates near the Quartz Crucible Wall Coated with Silicon Nitride in Cast-Grown Silicon. Applied Physics Express, 2013, 6, 081303.	2.4	6
138	Super-Resolution Raman Spectroscopy by Digital Image Processing. Journal of Spectroscopy, 2013, 2013, 1-9.	1.3	6
139	Evaluation of phonon confinement in ultrathin-film silicon-on-insulator by Raman spectroscopy. Japanese Journal of Applied Physics, 2014, 53, 032401.	1.5	6
140	Ge homoepitaxial growth by metal-organic chemical vapor deposition using t-C ₄ H ₉ GeH ₃ . Japanese Journal of Applied Physics, 2014, 53, 110301.	1.5	6
141	Influence of Al ₂ O ₃ layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	6
142	Relationship between passivation properties and band alignment in O ₃ -based atomic-layer-deposited AlO _x crystalline Si for photovoltaic applications. Japanese Journal of Applied Physics, 2015, 54, 08KD19.	1.5	6
143	Role of H ₂ supply for Sn incorporations in MOCVD Ge _{1-x} Sn _x epitaxial growth. Journal of Crystal Growth, 2017, 468, 605-609.	1.5	6
144	Enhanced nickelidation rate in silicon nanowires with interfacial lattice disorder. Journal of Applied Physics, 2017, 122, .	2.5	6

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145	Band gap-tuned MoS ₂ (1-x)Te _{2x} thin films synthesized by a hybrid Co-sputtering and post-deposition tellurization annealing process. Journal of Materials Research, 2017, 32, 3021-3028.	2.6	6
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